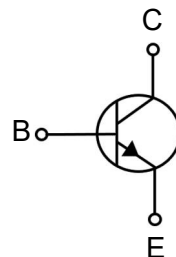
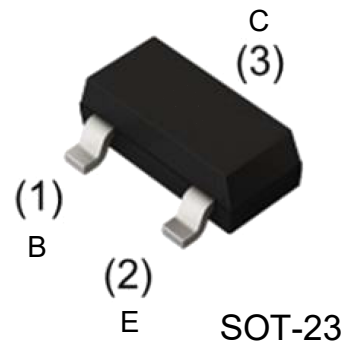


NPN Plastic-Encapsulate Transistors

FEATURES

- Collector Current: $I_C=0.5A$
- Power Dissipation of 200mW



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

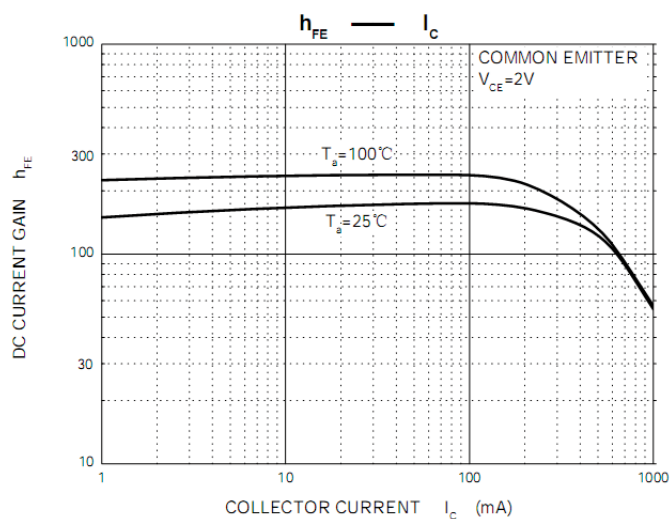
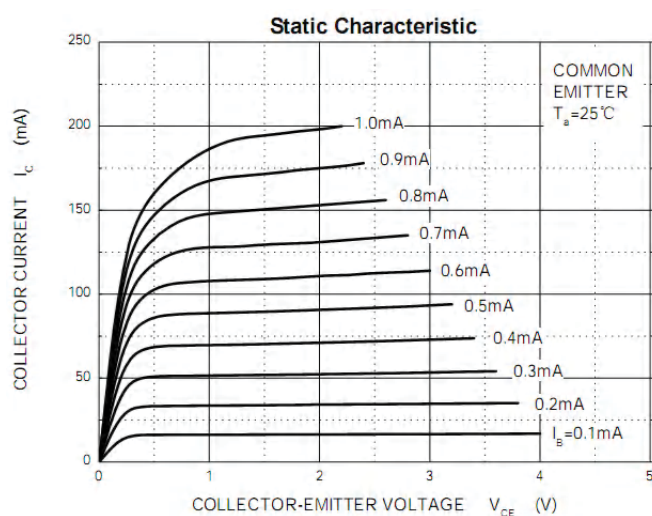
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	0.5	A
Collector Power Dissipation	P_C	0.2	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	83.3	$^{\circ}C/W$
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 ~ +150	$^{\circ}C$

NPN Plastic-Encapsulate Transistors

ELECTRICAL CHARACTERISTICS $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}, I_E = 0$	120		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	120		V
Base-emitter breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30\text{V}, I_E = 0$		100	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2\text{V}, I_C = 5\text{mA}$	205		
	$h_{FE(2)}$	$V_{CE} = 2\text{V}, I_C = 150\text{mA}$	210	250	
	$h_{FE(3)}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	205		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$		1	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$	100		MHz

Typical Characteristics



NPN Plastic-Encapsulate Transistors

